

Product Overview

MC14012B: Dual 4-Input NAND Gates

For complete documentation, see the data sheet.

These Dual 4 Input NAND Gates are constructed with P and N channel enhancement mode devices in a single monolithic structure (Complementary MOS). Their primary use is where low power dissipation and/or high noise immunity is desired.

Features

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- All Outputs Buffered
- Capable of Driving Two Low-power TTL Loads or One Low-power Schottky TTL Load Over the Rated Temperature Range.
- Double Diode Protection on All Inputs
- Pin-for-Pin Replacements for Corresponding CD4000 Series B Suffix Devices
- Pb-Free Packages are Available*

For more information please contact your local sales support at www.onsemi.com.

Created on: 7/30/2021